

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of fabricating a device using a lithographic process, the method comprising:

exposing a part of ~~a the~~ resist layer on a substrate to ultraviolet radiation; and
applying an electric field across the resist, the direction of the field being substantially perpendicular to a plane of the resist layer during the exposing.

2. (Original) A method according to claim 1, further comprising applying a layer of conductive material to an upper surface of the resist layer.

3. (Original) A method according to claim 2, wherein said electric field is applied by connecting said conductive layer to a fixed potential.

4. (Original) A method according to claim 2, wherein said conductive material is metallic.

5. (Original) A method according to claim 4, further comprising applying said layer of conductive material to a thickness of less than 50nm.

6. (Original) A method according to claim 2, wherein said layer of conductive material overlaps a side or base of the device.

7. (Original) A method according to claim 1, further comprising:
providing a layer of conductive material on a lower surface of the resist, between the resist and the surface of the device; and

applying said electric field during exposure by connecting the layer of conductive material to a fixed potential.

8. (Original) A method according to claim 7, wherein said layer of conductive material overlaps a side or base of the device.

9. (Original) A method according to claim 1, further comprising:
applying a layer of conductive material to an upper surface of the resist;
providing a layer of conductive material on a lower surface of the resist, between the resist and the surface of the device; and
applying said electric field during exposure by applying a potential difference between the two conducting layers.

10. (Original) A method according to claim 1, further comprising applying an electric field across the resist by directly coupling the resist to a fixed potential.

11. (Original) A method according to claim 8, further comprising incorporating a conducting material into the resist.

12. (Original) A method according to claim 1, wherein said radiation is in the extreme ultra-violet range.

13. (Currently Amended) A method according to claim 1, further comprising orienting the electric field such that an ~~the~~ upper surface of the resist layer is at a positive potential with respect to a ~~the~~ lower surface.

14. (Currently Amended) A lithographic apparatus comprising:
an illumination system configured to condition~~for providing~~ a projection beam of ultraviolet radiation;
a support structure configured to support ~~for supporting~~ a patterning device to impart ~~for imparting~~ a pattern to the projection beam;
a substrate table configured to hold ~~for holding~~ a substrate;
a projection system configured to project ~~for projecting~~ the patterned beam onto a target portion of the substrate; and

an electric field generator configured and arranged to apply an electric field across a resist layer provided on a surface of said substrate, the direction of said field being substantially perpendicular to the plane of the resist layer.

15. (Original) A method of fabricating a device using a lithographic process, comprising:

applying a radiation sensitive resist on top of the device, the resist material incorporating a conductive material; and

exposing a part of the resist to radiation while applying an electric field across the resist.

16. (Currently Amended) A method of processing a device using a lithographic process, said device comprising a radiation sensitive and conductive resist material, said method comprising:

exposing the resist material to UV-~~or EUV~~ radiation while applying an electric field across the resist material.

17. (New) The apparatus of claim 14, wherein the electric field generator is configured to apply said electric field by connecting a layer of conductive material on an upper surface of the resist layer to a fixed potential.

18. (New) The apparatus of claim 14, wherein the electric field generator is configured to apply said electric field by applying a potential difference between a layer of conductive material on an upper surface of the resist layer and a layer of conductive material on a lower surface of the resist layer, between the resist layer and the surface of the device.

19. (New) The apparatus of claim 14, wherein said radiation is in the extreme ultra-violet range.

20. (New) The method of claim 15, further comprising applying an electric field across the resist by directly coupling the resist to a fixed potential.

21. (New) The method of claim 15, wherein said radiation is in the extreme ultra-violet range.

22. (New) The method of claim 16, further comprising applying an electric field across the resist by directly coupling the resist to a fixed potential.

23. (New) The method of claim 16, wherein said radiation is in the extreme ultra-violet range.